

Orange Peel coupling in granular ferromagnetic films

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We present magnetoresistance (MR) measurements performed on magnetic tunnel junctions in which one of the electrodes is a granular ferromagnetic film. These junctions exhibit a zero field resistance dip. The dip magnitude depends on the size of the grains. We interpret these results as a consequence of the orange peel effect between the continuous ferromagnetic film and the magnetic grains. The coupling is found to be much stronger than that between continuous ferromagnetic layers.

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GMR (giant magnetoresistance) and TMR (tunneling magnetoresistance) devices are primary candidates in future magneto-electronic applications and media [1, 2, 3, 4, 5]. The ability to create arrays of magnetic junctions on micro sized areas can enhance storage size drastically and enable the production of non volatile ultra-dense RAM chips. Granular ferromagnets have a promising potential to act as a further step in this direction since a single junction may be able support numerous bits, considerably increasing the possible storage densities.

All applications based on GMR and TMR effects require high quality multilayers constructed of thin ferromagnetic and non-magnetic films. The performance of the devices depend strongly on the morphological and structural properties of the films as well as their physical characteristics. Among the crucial factors is the interlayer coupling between two ferromagnetic layers separated by a non-magnetic spacer. This coupling may be a sum of several different mechanisms, of which three appear to be dominant. The first is pinhole coupling, which results from structural defects in the spacer and may destroy MR effects altogether. The second is the RKKY interaction which oscillates with the spacer thickness. This coupling is due to indirect exchange mechanism and applies only to conductive barriers (GMR multilayers). The third mechanism is the Neel coupling [6], also named Orange Peel Effect (OPE), which applies both to conducting and to insulating spacers. This coupling utilizes the surface waviness of correlated layers to produce ferromagnetic interaction between ferromagnetic layers that could otherwise be antiferromagnetically coupled. The mechanism is based on the fact that the waviness of the magnetic film creates dipoles on the surface. A second layer with correlated waviness placed on top and separated by a non-magnetic spacer, experiences similar moment orientation due to dipole-dipole interaction as illustrated in figure 1a. Such ferromagnetic coupling reduces the GMR signal which requires antiferromagnetic orientation at low fields. Hence, a lot of effort is invested in an attempt to minimize this coupling in order to improve the performance of GMR/TMR elements [7, 8, 9, 10, 11, 12].

The basic Neel model was derived for two infinitely thick magnetic layers separated by a non magnetic spacer

[6]. Kools et al [13] extended the theory to included the finite size of the magnetic layers and obtained the following expression for the coupling strength:

$$H_{Neel} = \frac{2h^2 M_P}{2t_F} \left[1 - \exp\left(-\frac{2P}{2t_F}\right) \right] \exp\left(-\frac{2P}{2t_P}\right) \exp\left(-\frac{2P}{2t_S}\right) \quad (1)$$

where h and λ are the amplitude and wavelength of the layer waviness. t_F , t_P and t_S are the thicknesses of the free layer, the pinned layer and the spacer respectively, and M_P is the magnetization of the pinned layer.

So far, Neel coupling was studied only between continuous ferromagnetic layers. One may ask whether a similar effect can take place between a ferromagnetic layer and a set of ferromagnetic grains. This issue can be of great importance for the design of magnetic devices based on granular structures. A priori there seems to be no reason why OPE should not apply to granular systems providing the size of the grains correlates with the surface roughness of the layer. A schematic description of such a possible coupling is depicted in figure 1b. In this paper we describe an experimental effort to explore the OPE in granular systems. We present magnetoresistance measurements of magnetic tunnel junctions consisting of a uniform Ni layer, an insulating spacer and a granular Ni film. These structures exhibit a sharp magnetoresistance dip at low magnetic fields which are interpreted as signs for the OPE in the single domain grains.

The samples were prepared using the following scheme: First, a 250Å thick Ni layer was e-beam evaporated on a Si/SiO₂ substrate through a 1mm wide mask. The deposition rate was 0.5 Å/s and the base vacuum was 10⁻⁷ Torr. Next, a 100Å layer of SiO₂ was deposited in a 10⁻⁴ mbar oxygen environment through a 0.25mm wire-shape window leaving a narrow slit on top of the Ni layer. A 30Å thick Al₂O₃ (the insulating spacer) was then deposited into the window in a 10⁻⁴ mbar O₂ environment and at a rate of 0.2 Å/s. The quality of the barrier was confirmed by measuring the I-V curves of similar based Ni/Al₂O₃/Pb superconducting junctions. Finally a discontinuous Ni film was grown on top through a narrow strip shadow mask vertical to the continuous Ni layer, thus completing a 4 terminal junction geometry of 0.2

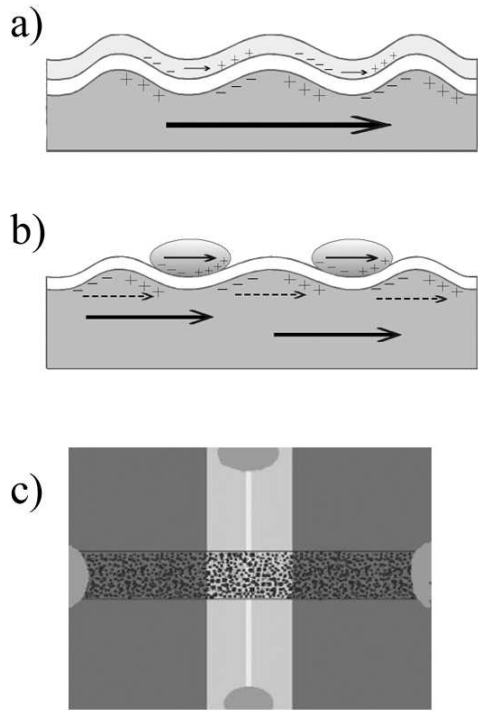


FIG. 1: a) Schematic description of the orange peel model for two finite continuous layers. Poles created on the surface of the bottom layer (pinned) induce compatible moments in the upper layer (free), thus creating artificial magnetic orientation. b) The possible orange peel model with a granular layer functioning as the free layer. The grain size is of the order of the waviness. Here the poles induced by the pinned layer create artificial magnetic orientations on individual grains. c) A sketch of the junction geometry.

nm^2 as illustrated in figure 1c.

A major concern with the granular system is the prevention of structural and chemical changes of the film due to oxidation or annealing. In order to circumvent these problems we prepared the granular films using the technique of quench condensation, i.e. evaporation on a cryo-cooled substrate within the measurement probe under ultra high vacuum conditions [14, 15, 16, 17]. This technique enables the growth of ultra-clean stable Ni grains with an excellent control over the inter-grain distance and the film resistance [18, 19]. For our junctions we quench condensed Ni discontinuous film on a substrate held at $T = 5\text{K}$ and with deposition rate ranging between $0.03\text{--}1\text{Å/s}$. As will be shown later the average grain size depends upon this rate. The sample resistance and thickness were measured during growth and the process was stopped at a desired resistance of $30\text{--}300\text{K}\Omega$. This resistance range insured that the film had an insulating granular geometry but, on the other hand, its resistance

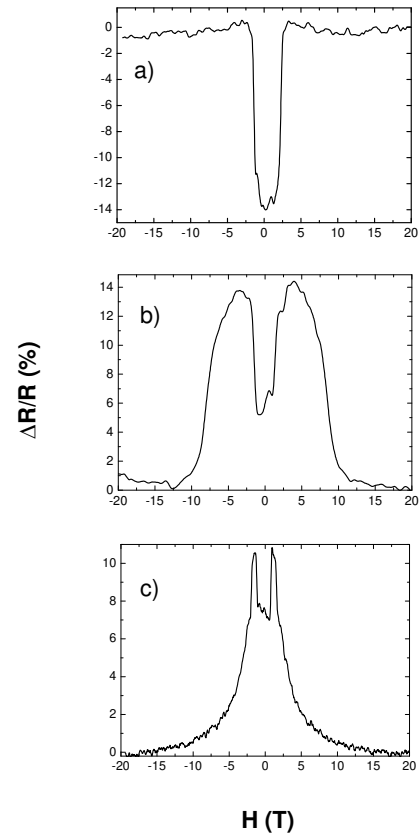


FIG. 2: MR curves of three typical tunnel junctions in which the granular films were deposited at different rates: 1, 0.3 and 0.03Å/s , for a) b) and c) respectively. Notice the difference in the magnitude of the zero field resistance dip. The faster the evaporation rate the larger the dip.

was much smaller than that of the junction (a few $\text{M}\Omega$), thus ensuring that the granular layer can be regarded as an equipotential electrode.

MR studies were performed at $T = 4\text{K}$ with external field applied perpendicular to the junction's plane. All measurements were performed using standard lock-in AC techniques and making sure that the I-V curves were in the ohmic regime. Figure 2 depicts the MR curve of 3 typical junctions in which the granular film was evaporated at rates of 1, 0.3 and 0.03Å/s . It is seen that the samples exhibit the following main features: As the field is reduced from high fields to below 1.2T a resistance rise of 2-15% is observed. This rise is rather gradual and extends up to about 0.4T . Further reducing the field below 0.2T causes a sharp resistance drop so that the MR curve exhibits a resistance dip around $H = 0$. We note that all of our measured samples exhibited these features. However, the magnitudes of the low field resistance minimum as well as the high field features depended strongly on the deposition rate of the granular film.

The high field resistance increase with decreasing magnetic field can be expected. The grain anisotropy may be different than that of the continuous film, hence, the

grains may switch their magnetic orientation at fields much larger than that of the continuous film. This leads to a resistance increase. We note that the fact that this feature extends to relatively large fields is unusual for Ni where all elements are expected to reach saturation at fields of $H = 0.6\text{T}$: In a different study we suggest [20] that these unusually high fields are a result of the existence of ultra small grains that experience unusual high coercivity.

The sharp resistance dip at small fields is more surprising. For this field range the magnetic elements of the junction are expected to be randomly oriented and the resistance is expected to exhibit a maximum. The sharp minimum at $H = 0$ is indicative of magnetic alignment of the continuous film with the grains on top. This requires a mechanism for low field ferromagnetic coupling between the uniform Ni film and the granular Ni system. A natural candidate is the O range Peelle effect. As noted above, this effect was extensively studied for systems containing two ferromagnetic layers. If a similar mechanism is relevant in a multilayer containing a granular film, the thickness roughness of the continuous film has to correlate with the grain average size. Figure 3 shows AFM analysis of a continuous Ni film and of granular films deposited at different deposition rates. It is important to note that it is very difficult to obtain exact morphological information on the quench-condensed granular films. As the system is heated to room temperature the films may experience some degree of creep and grains may slightly move. However, the AFM pictures can provide a good approximation for the structural features of the system. Figure 3 illustrates that the thickness roughness of our continuous layers has a wavelength of about 400-500 Å. For the granular systems, the average grain size grows as a function of deposition rate and approaches the wavelength of the continuous layer roughness for the fastest deposited films. A comparison between figures 2 and 3 reveals a clear correlation between the size of the grains and the amplitude of the zero bias dip in figure 2. The larger the grains (and the closer their size to the scale of the roughness in the continuous layer) the larger the dip. Granular systems which were grown at a rate of 1 Å/s have an average size of 400 Å and exhibit a dip magnitude of about 15% (figures 2a and 3a). For a deposition rate of 0.3 Å/s we get grain sizes of about 320 Å and a dip of 8% (figures 2b and 3b) and for a rate of 0.03 Å/s the sizes are 250 Å and the dip is 4% (figures 2c and 3c).

This correlation is in agreement with our notion that the resistance dip is due to Neel coupling between the continuous layer and grains on top. We envision that at very high fields both the continuous and the granular films are oriented parallel to the field direction and the resistance is low. As the field is reduced magnetic moments in the smallest grains start falling into the plain thus increasing the resistance. This process continues down to fields of the order of 0.4 T in which the magnetic

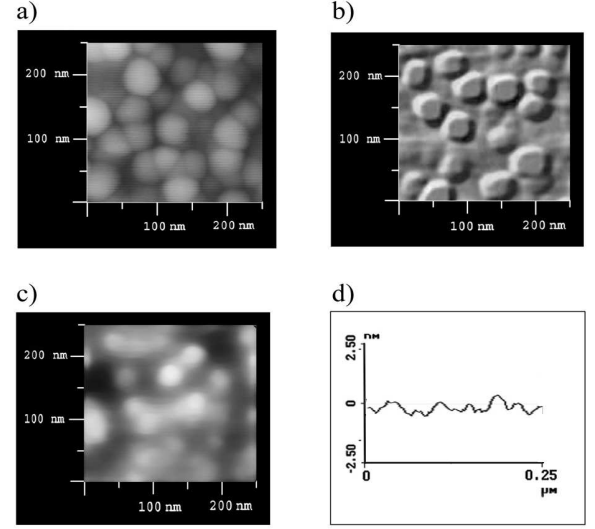


FIG. 3: AFM analysis of our layers. a b and c are AFM images of granular Ni films evaporated at rates of 1, 0.3 and 0.03 Å/s respectively (corresponding to the samples of figure 2a, 2b and 2c). d is the line scan of a continuous 250 Å thick Ni film.

moments of the continuous film start spraying into the plain. At fields below 0.2 T the OPE becomes important and each grain moment aligns itself with the moment of the domain placed below. This leads to the resistance dip at $H = 0$.

A feature which remains peculiar is the fact that for the high deposition rate samples (figure 2a) the resistance at $H = 0$ may be smaller than the high field value. One would expect that at high fields all elements are aligned and the resistance should be minimal. We note that such anomalies were seen in very dilute granular films [21]. In these samples the high field resistance was often higher than the zero field state. This effect was ascribed to magnetic dipole-dipole repulsion that the grains experience when they are aligned perpendicular to the substrate. We propose similar considerations in our junction geometry. As grains start aligning parallel to each other, all perpendicular to the substrate, dipole-dipole interactions cause magnetic repulsion between the grain moments which are aligned parallel to each other. This repulsion prevents the dipoles from being fully aligned and therefore the resistance of the junction is not at its minimum at high fields. At low fields the OPE aligns the grains parallel to the bottom continuous layer and the above reasoning is not relevant, hence a lower tunneling resistance may occur. If indeed the cause for the resistance dip is the OPE we can estimate its strength using equation 1. Based on our AFM images we use the following geometrical values: $h = 20\text{Å}$, $l = 400\text{Å}$, $t_F = 25\text{Å}$, $t_P = 250\text{Å}$ and $t_S = 25\text{Å}$. M_p for Ni is 560 esu/cc to yield a coupling strength of

$H_{N\text{eel}} \approx 600$ Oe. This value is similar to coupling strengths estimated and measured in continuous layer structures in which the OPE was studied. Our experimental results, however show that the coupling field scale extends to magnetic fields of approximately 2000 Oe. This large coupling scale seems to be a unique feature of our granular systems. Figure 2 demonstrates that although the magnitude of the dip depends on the deposition rate of the grains, the field scale of the effect is similar for all granular systems. This peculiar feature requires further theoretical treatment.

In conclusion we have measured the magnetoresistance properties of a multilayer containing continuous and granular Ni films separated by an insulating barrier. These exhibit a low field resistance dip which is indicative of a ferromagnetic coupling between the films. The coupling becomes stronger, the larger the correlation between the grain size and the surface roughness of the continuous film. We interpret these findings as signs for the Neel coupling taking place between the continuous film and the grains. The coupling seems to be much stronger than that between two continuous layers.

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